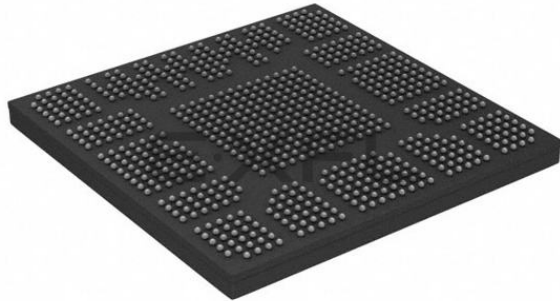




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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details

Product Status	Active
Number of LABs/CLBs	21000
Number of Logic Elements/Cells	84000
Total RAM Bits	3833856
Number of I/O	365
Number of Gates	-
Voltage - Supply	1.045V ~ 1.155V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	756-FBGA
Supplier Device Package	756-CABGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lfe5um5g-85f-8bg756c

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Acronyms in This Document

A list of acronyms used in this document.

Acronym	Definition
ALU	Arithmetic Logic Unit
BGA	Ball Grid Array
CDR	Clock and Data Recovery
CRC	Cycle Redundancy Code
DCC	Dynamic Clock Control
DCS	Dynamic Clock Select
DDR	Double Data Rate
DLL	Delay-Locked Loops
DSP	Digital Signal Processing
EBR	Embedded Block RAM
ECLK	Edge Clock
FFT	Fast Fourier Transforms
FIFO	First In First Out
FIR	Finite Impulse Response
LVCMOS	Low-Voltage Complementary Metal Oxide Semiconductor
LVDS	Low-Voltage Differential Signaling
LVPECL	Low Voltage Positive Emitter Coupled Logic
LVTTTL	Low Voltage Transistor-Transistor Logic
LUT	Look Up Table
MLVDS	Multipoint Low-Voltage Differential Signaling
PCI	Peripheral Component Interconnect
PCS	Physical Coding Sublayer
PCLK	Primary Clock
PDPR	Pseudo Dual Port RAM
PFU	Programmable Functional Unit
PIC	Programmable I/O Cells
PLL	Phase-Locked Loops
POR	Power On Reset
SCI	SERDES Client Interface
SERDES	Serializer/Deserializer
SEU	Single Event Upset
SLVS	Scalable Low-Voltage Signaling
SPI	Serial Peripheral Interface
SPR	Single Port RAM
SRAM	Static Random-Access Memory
TAP	Test Access Port
TDM	Time Division Multiplexing

1. General Description

The ECP5/ECP5-5G family of FPGA devices is optimized to deliver high performance features such as an enhanced DSP architecture, high speed SERDES (Serializer/Deserializer), and high speed source synchronous interfaces, in an economical FPGA fabric. This combination is achieved through advances in device architecture and the use of 40 nm technology making the devices suitable for high-volume, high-speed, and low-cost applications.

The ECP5/ECP5-5G device family covers look-up-table (LUT) capacity to 84K logic elements and supports up to 365 user I/Os. The ECP5/ECP5-5G device family also offers up to 156 18 x 18 multipliers and a wide range of parallel I/O standards.

The ECP5/ECP5-5G FPGA fabric is optimized high performance with low power and low cost in mind. The ECP5/ ECP5-5G devices utilize reconfigurable SRAM logic technology and provide popular building blocks such as LUT-based logic, distributed and embedded memory, Phase-Locked Loops (PLLs), Delay-Locked Loops (DLLs), pre-engineered source synchronous I/O support, enhanced sysDSP slices and advanced configuration support, including encryption and dual-boot capabilities.

The pre-engineered source synchronous logic implemented in the ECP5/ECP5-5G device family supports a broad range of interface standards including DDR2/3, LPDDR2/3, XGMII, and 7:1 LVDS.

The ECP5/ECP5-5G device family also features high speed SERDES with dedicated Physical Coding Sublayer (PCS) functions. High jitter tolerance and low transmit jitter allow the SERDES plus PCS blocks to be configured to support an array of popular data protocols including PCI Express, Ethernet (XAUI, GbE, and SGMII) and CPRI. Transmit De-emphasis with pre- and post-cursors, and Receive Equalization settings make the SERDES suitable for transmission and reception over various forms of media.

The ECP5/ECP5-5G devices also provide flexible, reliable and secure configuration options, such as dual-boot capability, bit-stream encryption, and TransFR field upgrade features.

ECP5-5G family devices have made some enhancement in the SERDES compared to ECP5UM devices. These enhancements increase the performance of the SERDES to up to 5 Gb/s data rate.

The ECP5-5G family devices are pin-to-pin compatible with the ECP5UM devices. These allows a migration path for users to port designs from ECP5UM to ECP5-5G devices to get higher performance.

The Lattice Diamond™ design software allows large complex designs to be efficiently implemented using the ECP5/ECP5-5G FPGA family. Synthesis library support for ECP5/ECP5-5G devices is available for popular logic synthesis tools. The Diamond tools use the synthesis tool output along with the constraints from its floor planning tools to place and route the design in the ECP5/ECP5-5G device. The tools extract the timing from the routing and back-annotate it into the design for timing verification.

Lattice provides many pre-engineered IP (Intellectual Property) modules for the ECP5/ECP5-5G family. By using these configurable soft core IPs as standardized blocks, designers are free to concentrate on the unique aspects of their design, increasing their productivity.

1.1. Features

- Higher Logic Density for Increased System Integration
 - 12K to 84K LUTs
 - 197 to 365 user programmable I/Os
- Embedded SERDES
 - 270 Mb/s, up to 3.2 Gb/s, SERDES interface (ECP5)
 - 270 Mb/s, up to 5.0 Gb/s, SERDES interface (ECP5-5G)
 - Supports eDP in RDR (1.62 Gb/s) and HDR (2.7 Gb/s)
 - Up to four channels per device: PCI Express, Ethernet (1GbE, SGMII, XAUI), and CPRI
- sysDSP™
 - Fully cascadable slice architecture
 - 12 to 160 slices for high performance multiply and accumulate
 - Powerful 54-bit ALU operations
 - Time Division Multiplexing MAC Sharing
 - Rounding and truncation
 - Each slice supports
 - Half 36 x 36, two 18 x 18 or four 9 x 9 multipliers
 - Advanced 18 x 36 MAC and 18 x 18 Multiply-Multiply-Accumulate (MMAC) operations
- Flexible Memory Resources
 - Up to 3.744 Mb sysMEM™ Embedded Block RAM (EBR)
 - 194K to 669K bits distributed RAM
- sysCLOCK Analog PLLs and DLLs

- Four DLLs and four PLLs in LFE5-45 and LFE5-85; two DLLs and two PLLs in LFE5-25 and LFE5-12
- Pre-Engineered Source Synchronous I/O
 - DDR registers in I/O cells
 - Dedicated read/write levelling functionality
 - Dedicated gearing logic
 - Source synchronous standards support
 - ADC/DAC, 7:1 LVDS, XGMII
 - High Speed ADC/DAC devices
 - Dedicated DDR2/DDR3 and LPDDR2/LPDDR3 memory support with DQS logic, up to 800 Mb/s data-rate
- Programmable sysI/O™ Buffer Supports Wide Range of Interfaces
 - On-chip termination
 - LVTTTL and LVCMOS 33/25/18/15/12
 - SSTL 18/15 I, II
 - HSUL12
 - LVDS, Bus-LVDS, LVPECL, RSDS, MLVDS
 - subLVDS and SLVS, MIPI D-PHY input interfaces
- Flexible Device Configuration
 - Shared bank for configuration I/Os
 - SPI boot flash interface
 - Dual-boot images supported
 - Slave SPI
 - TransFR™ I/O for simple field updates
- Single Event Upset (SEU) Mitigation Support
 - Soft Error Detect – Embedded hard macro
 - Soft Error Correction – Without stopping user operation
 - Soft Error Injection – Emulate SEU event to debug system error handling
- System Level Support
 - IEEE 1149.1 and IEEE 1532 compliant
 - Reveal Logic Analyzer
 - On-chip oscillator for initialization and general use
 - 1.1 V core power supply for ECP5, 1.2 V core power supply for ECP5UM5G

Table 1.1. ECP5 and ECP5-5G Family Selection Guide

Device	LFE5UM-25 LFE5UM5G-25	LFE5UM-45 LFE5UM5G-45	LFE5UM-85 LFE5UM5G-85	LFE5U- 12	LFE5U- 25	LFE5U- 45	LFE5U- 85
LUTs (K)	24	44	84	12	24	44	84
sysMEM Blocks (18 Kb)	56	108	208	32	56	108	208
Embedded Memory (Kb)	1,008	1944	3744	576	1,008	1944	3744
Distributed RAM Bits (Kb)	194	351	669	97	194	351	669
18 X 18 Multipliers	28	72	156	28	28	72	156
SERDES (Dual/Channels)	1/2	2/4	2/4	0	0	0	0
PLLs/DLLs	2/2	4/4	4/4	2/2	2/2	4/4	4/4
Packages (SERDES Channels / IO Count)							
256 caBGA (14 x 14 mm ² , 0.8 mm)	—	—	—	0/197	0/197	0/197	—
285 csfBGA (10 x 10 mm ² , 0.5 mm)	2/118	2/118	2/118	0/118	0/118	0/118	0/118
381 caBGA (17 x 17 mm ² , 0.8 mm)	2/197	4/203	4/205	0/197	0/197	0/203	0/205
554 caBGA (23 x 23 mm ² , 0.8 mm)	—	4/245	4/259	—	—	0/245	0/259
756 caBGA (27 x 27 mm ² , 0.8 mm)	—	—	4/365	—	—	—	0/365

2.7. DDRDLL

Every DDRDLL (master DLL block) can generate phase shift code representing the amount of delay in a delay block that corresponding to 90° phase of the reference clock input. The reference clock can be either from PLL, or input pin. This code is used in the DQSBUF block that controls a set of DQS pin groups to interface with DDR memory (slave DLL). There are two DDRDLLs that supply two sets of codes (for two different reference clock frequencies) to each side of the I/Os (at each of the corners). The DQSBUF uses this code to controls the DQS input of the DDR memory to 90° shift to clock DQs at the center of the data eye for DDR memory interface.

The code is also sent to another slave DLL, DLLDEL, that takes a clock input and generates a 90° shift clock output to drive the clocking structure. This is useful to interface edge-aligned Generic DDR, where 90° clocking needs to be created. Figure 2.10 shows DDRDLL functional diagram.

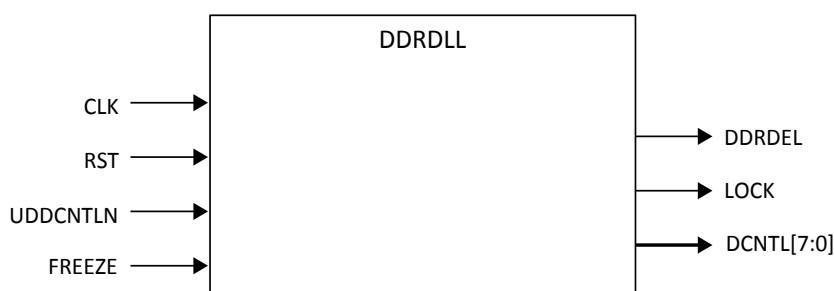


Figure 2.10. DDRDLL Functional Diagram

Table 2.5. DDRDLL Ports List

Port Name	Type	Description
CLK	Input	Reference clock input to the DDRDLL. Should run at the same frequency as the clock to the delay code.
RST	Input	Reset Input to the DDRDLL.
UDDCNTLN	Input	Update Control to update the delay code. The code is the DCNTL[7:0] outputs. These outputs are updated when the UDDCNTLN signal is LOW.
FREEZE	Input	FREEZE goes high and, without a glitch, turns off the DLL internal clock and the ring oscillator output clock. When FREEZE goes low, it turns them back on.
DDRDEL	Output	The delay codes from the DDRDLL to be used in DQSBUF or DLLDEL.
LOCK	Output	Lock output to indicate the DDRDLL has valid delay output.
DCNTL [7:0]	Output	The delay codes from the DDRDLL available for the user IP.

There are four identical DDRDLLs, one in each of the four corners in LFE5-85 and LFE5-45 devices, and two DDRDLLs in both LFE5-25 & LFE5-12 devices in the upper two corners. Each DDRDLL can generate delay code based on the reference frequency. The slave DLL (DQSBUF and DLLDEL) use the code to delay the signal, to create the phase shifted signal used for either DDR memory, to create 90° shift clock. Figure 2.11 shows the DDRDLL and the slave DLLs on the top level view.

2.14. sysI/O Buffer

Each I/O is associated with a flexible buffer referred to as a sysI/O buffer. These buffers are arranged around the periphery of the device in groups referred to as banks. The sysI/O buffers allow users to implement the wide variety of standards that are found in today's systems including LVDS, HSUL, BLVDS, SSTL Class I and II, LVCMOS, LVTTTL, LVPECL, and MIPI.

2.14.1. sysI/O Buffer Banks

ECP5/ECP5-5G devices have seven sysI/O buffer banks, two banks per side at Top, Left and Right, plus one at the bottom left side. The bottom left side bank (Bank 8) is a shared I/O bank. The I/Os in that bank contains both dedicated and shared I/O for sysConfig function. When a shared pin is not used for configuration, it is available as a user I/O. For LFE5-85 devices, there is an additional I/O bank (Bank 4) that is not available in other device in the family.

In ECP5/ECP5-5G devices, the Left and Right sides are tailored to support high performance interfaces, such as DDR2, DDR3, LPDDR2, LPDDR3 and other high speed source synchronous standards. The banks on the Left and Right sides of the devices feature LVDS input and output buffers, data-width gearing, and DQSBUF block to support DDR2/3 and LPDDR2/3 interfaces. The I/Os on the top and bottom banks do not have LVDS input and output buffer, and gearing logic, but can use LVCMOS to emulate most of differential output signaling.

Each sysIO bank has its own I/O supply voltage (V_{CCIO}). In addition, the banks on the Left and Right sides of the device, have voltage reference input (shared I/O pin), V_{REF1} per bank, which allow it to be completely independent of each other. The V_{REF} voltage is used to set the threshold for the referenced input buffers, such as SSTL. Figure 2.25 shows the seven banks and their associated supplies.

In ECP5/ECP5-5G devices, single-ended output buffers and ratioed input buffers (LVTTTL, and LVCMOS) are powered using V_{CCIO} . LVTTTL, LVCMOS33, LVCMOS25 and LVCMOS12 can also be set as fixed threshold inputs independent of V_{CCIO} .

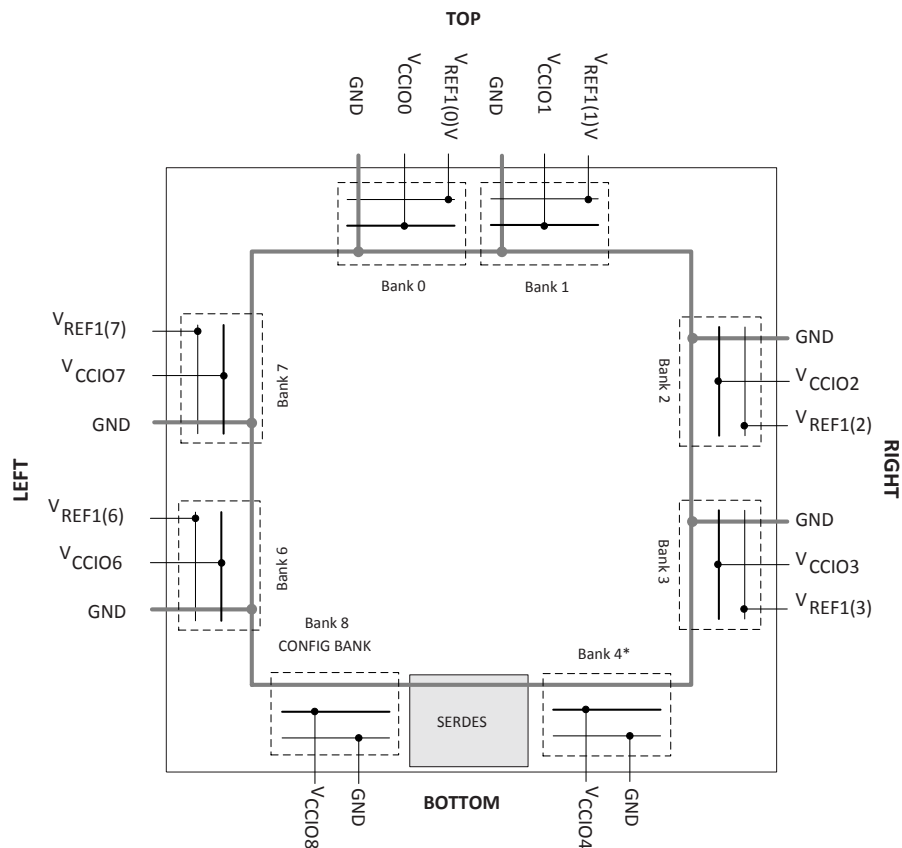


Figure 2.25. ECP5/ECP5-5G Device Family Banks

2.18. Device Configuration

All ECP5/ECP5-5G devices contain two ports that can be used for device configuration. The Test Access Port (TAP), which supports bit-wide configuration, and the sysCONFIG port, support dual-byte, byte and serial configuration. The TAP supports both the IEEE Standard 1149.1 Boundary Scan specification and the IEEE Standard 1532 In-System Configuration specification. There are 11 dedicated pins for TAP and sysConfig supports (TDI, TDO, TCK, TMS, CFG[2:0], PROGRAMN, DONE, INITN and CCLK). The remaining sysCONFIG pins are used as dual function pins. Refer to [ECP5 and ECP5-5G sysCONFIG Usage Guide \(TN1260\)](#) for more information about using the dual-use pins as general purpose I/Os.

There are various ways to configure an ECP5/ECP5-5G device:

- JTAG
- Standard Serial Peripheral Interface (SPI) – Interface to boot PROM Support x1, x2, x4 wide SPI memory interfaces.
- System microprocessor to drive a x8 CPU port SPCM mode
- System microprocessor to drive a serial slave SPI port (SSPI mode)
- Slave Serial model (SCM)

On power-up, the FPGA SRAM is ready to be configured using the selected sysCONFIG port. Once a configuration port is selected, it will remain active throughout that configuration cycle. The IEEE 1149.1 port can be activated any time after power-up by sending the appropriate command through the TAP port.

ECP5/ECP5-5G devices also support the Slave SPI Interface. In this mode, the FPGA behaves like a SPI Flash device (slave mode) with the SPI port of the FPGA to perform read-write operations.

2.18.1. Enhanced Configuration Options

ECP5/ECP5-5G devices have enhanced configuration features such as: decryption support, decompression support, TransFR™ I/O and dual-boot and multi-boot image support.

TransFR (Transparent Field Reconfiguration)

TransFR I/O (TFR) is a unique Lattice technology that allows users to update their logic in the field without interrupting system operation using a single ispVM command. TransFR I/O allows I/O states to be frozen during device configuration. This allows the device to be field updated with a minimum of system disruption and downtime. Refer to [Minimizing System Interruption During Configuration Using TransFR Technology \(TN1087\)](#) for details.

Dual-Boot and Multi-Boot Image Support

Dual-boot and multi-boot images are supported for applications requiring reliable remote updates of configuration data for the system FPGA. After the system is running with a basic configuration, a new boot image can be downloaded remotely and stored in a separate location in the configuration storage device. Any time after the update the ECP5/ECP5-5G devices can be re-booted from this new configuration file. If there is a problem, such as corrupt data during download or incorrect version number with this new boot image, the ECP5/ECP5-5G device can revert back to the original backup golden configuration and try again. This all can be done without power cycling the system. For more information, refer to [ECP5 and ECP5-5G sysCONFIG Usage Guide \(TN1260\)](#).

2.18.2. Single Event Upset (SEU) Support

ECP5/ECP5-5G devices support SEU mitigation with three supporting functions:

- SED – Soft Error Detect
- SEC – Soft Error Correction
- SEI – Soft Error Injection

ECP5/ECP5-5G devices have dedicated logic to perform Cycle Redundancy Code (CRC) checks. During configuration, the configuration data bitstream can be checked with the CRC logic block. In addition, the ECP5/ECP5-5G device can also be programmed to utilize a Soft Error Detect (SED) mode that checks for soft errors in configuration SRAM. The SED operation can be run in the background during user mode. If a soft error occurs, during user mode (normal operation) the device can be programmed to generate an error signal.

3. DC and Switching Characteristics

3.1. Absolute Maximum Ratings

Table 3.1. Absolute Maximum Ratings

Symbol	Parameter	Min	Max	Unit
V _{CC}	Supply Voltage	−0.5	1.32	V
V _{CCA}	Supply Voltage	−0.5	1.32	V
V _{CCAUX} , V _{CCAUXA}	Supply Voltage	−0.5	2.75	V
V _{CCIO}	Supply Voltage	−0.5	3.63	V
—	Input or I/O Transient Voltage Applied	−0.5	3.63	V
V _{CCHRX} , V _{CCHTX}	SERDES RX/TX Buffer Supply Voltages	−0.5	1.32	V
—	Voltage Applied on SERDES Pins	−0.5	1.80	V
T _A	Storage Temperature (Ambient)	−65	150	°C
T _J	Junction Temperature	—	+125	°C

Notes:

1. Stress above those listed under the “Absolute Maximum Ratings” may cause permanent damage to the device. Functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.
2. Compliance with the Lattice [Thermal Management](#) document is required.
3. All voltages referenced to GND.

3.2. Recommended Operating Conditions

Table 3.2. Recommended Operating Conditions

Symbol	Parameter		Min	Max	Unit
V _{CC} ²	Core Supply Voltage	ECP5	1.045	1.155	V
		ECP5-5G	1.14	1.26	V
V _{CCAUX} ^{2,4}	Auxiliary Supply Voltage	—	2.375	2.625	V
V _{CCIO} ^{2,3}	I/O Driver Supply Voltage	—	1.14	3.465	V
V _{REF} ¹	Input Reference Voltage	—	0.5	1.0	V
t _{JCOM}	Junction Temperature, Commercial Operation	—	0	85	°C
t _{JIND}	Junction Temperature, Industrial Operation	—	−40	100	°C
SERDES External Power Supply⁵					
V _{CCA}	SERDES Analog Power Supply	ECP5UM	1.045	1.155	V
		ECP5-5G	1.164	1.236	V
V _{CCAUXA}	SERDES Auxiliary Supply Voltage	—	2.374	2.625	V
V _{CCHRX} ⁶	SERDES Input Buffer Power Supply	ECP5UM	0.30	1.155	V
		ECP5-5G	0.30	1.26	V
V _{CCHTX}	SERDES Output Buffer Power Supply	ECP5UM	1.045	1.155	V
		ECP5-5G	1.14	1.26	V

Notes:

1. For correct operation, all supplies except V_{REF} must be held in their valid operation range. This is true independent of feature usage.
2. All supplies with same voltage, except SERDES Power Supplies, should be connected together.
3. See recommended voltages by I/O standard in [Table 3.4](#) on page 48.
4. V_{CCAUX} ramp rate must not exceed 30 mV/μs during power-up when transitioning between 0 V and 3 V.
5. Refer to [ECP5 and ECP5-5G SERDES/PCS Usage Guide \(TN1261\)](#) for information on board considerations for SERDES power supplies.
6. V_{CCHRX} is used for Rx termination. It can be biased to V_{cm} if external AC coupling is used. This voltage needs to meet all the HDin input voltage level requirements specified in the Rx section of this Data Sheet.

3.3. Power Supply Ramp Rates

Table 3.3. Power Supply Ramp Rates

Symbol	Parameter	Min	Typ	Max	Unit
t_{RAMP}	Power Supply ramp rates for all supplies	0.01	—	10	V/ms

Note: Assumes monotonic ramp rates.

3.4. Power-On-Reset Voltage Levels

Table 3.4. Power-On-Reset Voltage Levels

Symbol	Parameter			Min	Typ	Max	Unit
V_{PORUP}	All Devices	Power-On-Reset ramp-up trip point (Monitoring V_{CC} , V_{CCAUX} , and V_{CCIO8})	V_{CC}	0.90	—	1.00	V
			V_{CCAUX}	2.00	—	2.20	V
			V_{CCIO8}	0.95	—	1.06	V
V_{PORDN}	All Devices	Power-On-Reset ramp-down trip point (Monitoring V_{CC} , and V_{CCAUX})	V_{CC}	0.77	—	0.87	V
			V_{CCAUX}	1.80	—	2.00	V

Notes:

- These POR trip points are only provided for guidance. Device operation is only characterized for power supply voltages specified under recommended operating conditions.
- Only V_{CCIO8} has a Power-On-Reset ramp up trip point. All other V_{CCIOs} do not have Power-On-Reset ramp up detection.
- V_{CCIO8} does not have a Power-On-Reset ramp down detection. V_{CCIO8} must remain within the Recommended Operating Conditions to ensure proper operation.

3.5. Power up Sequence

Power-On-Reset (POR) puts the ECP5/ECP5-5G device in a reset state. POR is released when V_{CC} , V_{CCAUX} , and V_{CCIO8} are ramped above the V_{PORUP} voltage, as specified above.

V_{CCIO8} controls the voltage on the configuration I/O pins. If the ECP5/ECP5-5G device is using Master SPI mode to download configuration data from external SPI Flash, it is required to ramp V_{CCIO8} above V_{IH} of the external SPI Flash, before at least one of the other two supplies (V_{CC} and/or V_{CCAUX}) is ramped to V_{PORUP} voltage level. If the system cannot meet this power up sequence requirement, and requires the V_{CCIO8} to be ramped last, then the system must keep either PROGRAMN or INITN pin LOW during power up, until V_{CCIO8} reaches V_{IH} of the external SPI Flash. This ensures the signals driven out on the configuration pins to the external SPI Flash meet the V_{IH} voltage requirement of the SPI Flash. For LFE5UM/LFE5UM5G devices, it is required to power up V_{CCA} , before V_{CCAUXA} is powered up.

3.6. Hot Socketing Specifications

Table 3.5. Hot Socketing Specifications

Symbol	Parameter	Condition	Min	Typ	Max	Unit
IDK_HS	Input or I/O Leakage Current for Top and Bottom Banks Only	$0 \leq V_{IN} \leq V_{IH} \text{ (Max)}$	—	—	± 1	mA
IDK	Input or I/O Leakage Current for Left and Right Banks Only	$0 \leq V_{IN} < V_{CCIO}$	—	—	± 1	mA
		$V_{CCIO} \leq V_{IN} \leq V_{CCIO} + 0.5 \text{ V}$	—	18	—	mA

Notes:

- V_{CC} , V_{CCAUX} and V_{CCIO} should rise/fall monotonically.
- I_{DK} is additive to I_{PU} , I_{PW} or I_{BH} .
- LVC MOS and LV TTL only.
- Hot socket specification defines when the hot socketed device's junction temperature is at 85 °C or below. When the hot socketed device's junction temperature is above 85 °C, the I_{DK} current can exceed ± 1 mA.

3.12. sysI/O Recommended Operating Conditions

Table 3.11. sysI/O Recommended Operating Conditions

Standard	V _{CCIO}			V _{REF} (V)		
	Min	Typ	Max	Min	Typ	Max
LVC MOS33 ¹	3.135	3.3	3.465	—	—	—
LVC MOS33D ³ Output	3.135	3.3	3.465	—	—	—
LVC MOS25 ¹	2.375	2.5	2.625	—	—	—
LVC MOS18	1.71	1.8	1.89	—	—	—
LVC MOS15	1.425	1.5	1.575	—	—	—
LVC MOS12 ¹	1.14	1.2	1.26	—	—	—
LVTTL33 ¹	3.135	3.3	3.465	—	—	—
SSTL15_I, _II ²	1.43	1.5	1.57	0.68	0.75	0.9
SSTL18_I, _II ²	1.71	1.8	1.89	0.833	0.9	0.969
SSTL135_I, _II ²	1.28	1.35	1.42	0.6	0.675	0.75
HSUL12 ²	1.14	1.2	1.26	0.588	0.6	0.612
MIPI D-PHY LP Input ^{3, 5}	1.425	1.5	1.575	—	—	—
LVDS25 ^{1, 3} Output	2.375	2.5	2.625	—	—	—
subLV ³ (Input only)	—	—	—	—	—	—
SLV ³ (Input only)	—	—	—	—	—	—
LVDS25E ³ Output	2.375	2.5	2.625	—	—	—
MLVDS ³ Output	2.375	2.5	2.625	—	—	—
LVPECL33 ^{1, 3} Output	3.135	3.3	3.465	—	—	—
BLVDS25 ^{1, 3} Output	2.375	2.5	2.625	—	—	—
HSULD12D ^{2, 3}	1.14	1.2	1.26	—	—	—
SSTL135D_I, II ^{2, 3}	1.28	1.35	1.42	—	—	—
SSTL15D_I, II ^{2, 3}	1.43	1.5	1.57	—	—	—
SSTL18D_I ^{1, 2, 3} , II ^{1, 2, 3}	1.71	1.8	1.89	—	—	—

Notes:

1. For input voltage compatibility, refer to [ECP5 and ECP5-5G sysIO Usage Guide \(TN1262\)](#).
2. V_{REF} is required when using Differential SSTL and HSUL to interface to DDR/LPDDR memories.
3. These differential inputs use LVDS input comparator, which uses V_{CCAUX} power
4. All differential inputs and LVDS25 output are supported in the Left and Right banks only. Refer to [ECP5 and ECP5-5G sysIO Usage Guide \(TN1262\)](#) for details.
5. MIPI D-PHY LP input can be implemented by powering VCCIO to 1.5V, and select MIPI LP primitive to meet MIPI Alliance spec on V_{IH} and V_{IL}. It can also be implemented as LVC MOS12 with VCCIO at 1.2V, which would meet V_{IH}/V_{IL} spec on LVCOM12.

3.17. Maximum I/O Buffer Speed

Over recommended operating conditions.

Table 3.21. ECP5/ECP5-5G Maximum I/O Buffer Speed

Buffer	Description	Max	Unit
Maximum Input Frequency			
LVDS25	LVDS, $V_{CCIO} = 2.5\text{ V}$	400	MHz
MLVDS25	MLVDS, Emulated, $V_{CCIO} = 2.5\text{ V}$	400	MHz
BLVDS25	BLVDS, Emulated, $V_{CCIO} = 2.5\text{ V}$	400	MHz
MIPI D-PHY (HS Mode)	MIPI Video	400	MHz
SLVS	SLVS similar to MIPI	400	MHz
Mini LVDS	Mini LVDS	400	MHz
LVPECL33	LVPECL, Emulated, $V_{CCIO} = 3.3\text{ V}$	400	MHz
SSTL18 (all supported classes)	SSTL_18 class I, II, $V_{CCIO} = 1.8\text{ V}$	400	MHz
SSTL15 (all supported classes)	SSTL_15 class I, II, $V_{CCIO} = 1.5\text{ V}$	400	MHz
SSTL135 (all supported classes)	SSTL_135 class I, II, $V_{CCIO} = 1.35\text{ V}$	400	MHz
HSUL12 (all supported classes)	HSUL_12 class I, II, $V_{CCIO} = 1.2\text{ V}$	400	MHz
LVTTL33	LVTTL, $V_{CCIO} = 3.3\text{ V}$	200	MHz
LVC MOS33	LVC MOS, $V_{CCIO} = 3.3\text{ V}$	200	MHz
LVC MOS25	LVC MOS, $V_{CCIO} = 2.5\text{ V}$	200	MHz
LVC MOS18	LVC MOS, $V_{CCIO} = 1.8\text{ V}$	200	MHz
LVC MOS15	LVC MOS 1.5, $V_{CCIO} = 1.5\text{ V}$	200	MHz
LVC MOS12	LVC MOS 1.2, $V_{CCIO} = 1.2\text{ V}$	200	MHz
Maximum Output Frequency			
LVDS25E	LVDS, Emulated, $V_{CCIO} = 2.5\text{ V}$	150	MHz
LVDS25	LVDS, $V_{CCIO} = 2.5\text{ V}$	400	MHz
MLVDS25	MLVDS, Emulated, $V_{CCIO} = 2.5\text{ V}$	150	MHz
BLVDS25	BLVDS, Emulated, $V_{CCIO} = 2.5\text{ V}$	150	MHz
LVPECL33	LVPECL, Emulated, $V_{CCIO} = 3.3\text{ V}$	150	MHz
SSTL18 (all supported classes)	SSTL_18 class I, II, $V_{CCIO} = 1.8\text{ V}$	400	MHz
SSTL15 (all supported classes)	SSTL_15 class I, II, $V_{CCIO} = 1.5\text{ V}$	400	MHz
SSTL135 (all supported classes)	SSTL_135 class I, II, $V_{CCIO} = 1.35\text{ V}$	400	MHz
HSUL12 (all supported classes)	HSUL12 class I, II, $V_{CCIO} = 1.2\text{ V}$	400	MHz
LVTTL33	LVTTL, $V_{CCIO} = 3.3\text{ V}$	150	MHz
LVC MOS33 (For all drives)	LVC MOS, 3.3 V	150	MHz
LVC MOS25 (For all drives)	LVC MOS, 2.5 V	150	MHz
LVC MOS18 (For all drives)	LVC MOS, 1.8 V	150	MHz
LVC MOS15 (For all drives)	LVC MOS, 1.5 V	150	MHz
LVC MOS12 (For all drives)	LVC MOS, 1.2 V	150	MHz

Notes:

1. These maximum speeds are characterized but not tested on every device.
2. Maximum I/O speed for differential output standards emulated with resistors depends on the layout.
3. LVC MOS timing is measured with the load specified in Switching Test Conditions, Table 3.44 on page 90.
4. All speeds are measured at fast slew.
5. Actual system operation may vary depending on user logic implementation.
6. Maximum data rate equals 2 times the clock rate when utilizing DDR.

3.18. External Switching Characteristics

Over recommended commercial operating conditions.

Table 3.22. ECP5/ECP5-5G External Switching Characteristics

Parameter	Description	Device	-8		-7		-6		Unit
			Min	Max	Min	Max	Min	Max	
Clocks									
Primary Clock									
f _{MAX_PRI}	Frequency for Primary Clock Tree	—	—	370	—	303	—	257	MHz
t _{W_PRI}	Clock Pulse Width for Primary Clock	—	0.8	—	0.9	—	1.0	—	ns
t _{SKEW_PRI}	Primary Clock Skew within a Device	—	—	420	—	462	—	505	ps
Edge Clock									
f _{MAX_EDGE}	Frequency for Edge Clock Tree	—	—	400	—	350	—	312	MHz
t _{W_EDGE}	Clock Pulse Width for Edge Clock	—	1.175	—	1.344	—	1.50	—	ns
t _{SKEW_EDGE}	Edge Clock Skew within a Bank	—	—	160	—	180	—	200	ps
Generic SDR Input									
General I/O Pin Parameters Using Dedicated Primary Clock Input without PLL									
t _{CO}	Clock to Output - PIO Output Register	All Devices	—	5.4	—	6.1	—	6.8	ns
t _{SU}	Clock to Data Setup - PIO Input Register	All Devices	0	—	0	—	0	—	ns
t _H	Clock to Data Hold - PIO Input Register	All Devices	2.7	—	3	—	3.3	—	ns
t _{SU_DEL}	Clock to Data Setup - PIO Input Register with Data Input Delay	All Devices	1.2	—	1.33	—	1.46	—	ns
t _{H_DEL}	Clock to Data Hold - PIO Input Register with Data Input Delay	All Devices	0	—	0	—	0	—	ns
f _{MAX_IO}	Clock Frequency of I/O and PFU Register	All Devices	—	400	—	350	—	312	MHz
General I/O Pin Parameters Using Dedicated Primary Clock Input with PLL									
t _{COPLL}	Clock to Output - PIO Output Register	All Devices	—	3.5	—	3.8	—	4.1	ns
t _{SUPLL}	Clock to Data Setup - PIO Input Register	All Devices	0.7	—	0.78	—	0.85	—	ns
t _{HPLL}	Clock to Data Hold - PIO Input Register	All Devices	0.8	—	0.89	—	0.98	—	ns
t _{SU_DEPLL}	Clock to Data Setup - PIO Input Register with Data Input Delay	All Devices	1.6	—	1.78	—	1.95	—	ns

Table 3.22. ECP5/ECP5-5G External Switching Characteristics (Continued)

Parameter	Description	Device	-8		-7		-6		Unit
			Min	Max	Min	Max	Min	Max	
Generic DDR Output									
Generic DDRX1 Outputs With Clock and Data Centered at Pin (GDDRX1_TX.SCLK.Centered) Using PCLK Clock Input - Figure 3.6									
t _{DVB_GDDRX1_centered}	Data Output Valid before CLK Output	All Devices	-0.67	—	-0.67	—	-0.67	—	ns + 1/2 UI
t _{DVA_GDDRX1_centered}	Data Output Valid after CLK Output	All Devices	-0.67	—	-0.67	—	-0.67	—	ns + 1/2 UI
f _{DATA_GDDRX1_centered}	GDDRX1 Data Rate	All Devices	—	500	—	500	—	500	Mb/s
f _{MAX_GDDRX1_centered}	GDDRX1 CLK Frequency (SCLK)	All Devices	—	250	—	250	—	250	MHz
Generic DDRX1 Outputs With Clock and Data Aligned at Pin (GDDRX1_TX.SCLK.Aligned) Using PCLK Clock Input - Figure 3.9									
t _{DIB_GDDRX1_aligned}	Data Output Invalid before CLK Output	All Devices	-0.3	—	-0.3	—	-0.3	—	ns
t _{DIA_GDDRX1_aligned}	Data Output Invalid after CLK Output	All Devices	—	0.3	—	0.3	—	0.3	ns
f _{DATA_GDDRX1_aligned}	GDDRX1 Data Rate	All Devices	—	500	—	500	—	500	Mb/s
f _{MAX_GDDRX1_aligned}	GDDRX1 CLK Frequency (SCLK)	All Devices	—	250	—	250	—	250	MHz
Generic DDRX2 Outputs With Clock and Data Centered at Pin (GDDRX2_TX.ECLK.Centered) Using PCLK Clock Input, Left and Right sides Only - Figure 3.8									
t _{DVB_GDDRX2_centered}	Data Output Valid Before CLK Output	All Devices	— 0.442	—	-0.56	—	— 0.676	—	ns + 1/2 UI
t _{DVA_GDDRX2_centered}	Data Output Valid After CLK Output	All Devices	—	0.442	—	0.56	—	0.676	ns + 1/2 UI
f _{DATA_GDDRX2_centered}	GDDRX2 Data Rate	All Devices	—	800	—	700	—	624	Mb/s
f _{MAX_GDDRX2_centered}	GDDRX2 CLK Frequency (ECLK)	All Devices	—	400	—	350	—	312	MHz
Generic DDRX2 Outputs With Clock and Data Aligned at Pin (GDDRX2_TX.ECLK.Aligned) Using PCLK Clock Input, Left and Right sides Only - Figure 3.9									
t _{DIB_GDDRX2_aligned}	Data Output Invalid before CLK Output	All Devices	-0.16	—	-0.18	—	-0.2	—	ns
t _{DIA_GDDRX2_aligned}	Data Output Invalid after CLK Output	All Devices	—	0.16	—	0.18	—	0.2	ns
f _{DATA_GDDRX2_aligned}	GDDRX2 Data Rate	All Devices	—	800	—	700	—	624	Mb/s
f _{MAX_GDDRX2_aligned}	GDDRX2 CLK Frequency (ECLK)	All Devices	—	400	—	350	—	312	MHz
Video DDRX71 Outputs With Clock and Data Aligned at Pin (GDDRX71_TX.ECLK) Using PLL Clock Input, Left and Right sides Only - Figure 3.12									
t _{DIB_LVDS71_i}	Data Output Invalid before CLK Output	All Devices	-0.16	—	-0.18	—	-0.2	—	ns + (i) * UI
t _{DIA_LVDS71_i}	Data Output Invalid after CLK Output	All Devices	—	0.16	—	0.18	—	0.2	ns + (i) * UI
f _{DATA_LVDS71}	DDR71 Data Rate	All Devices	—	756	—	620	—	525	Mb/s
f _{MAX_LVDS71}	DDR71 CLK Frequency (ECLK)	All Devices	—	378	—	310	—	262.5	MHz
Memory Interface									
DDR2/DDR3/DDR3L/LPDDR2/LPDDR3 READ (DQ Input Data are Aligned to DQS)									
t _{DVBQQ_DDR2} t _{DVBQQ_DDR3} t _{DVBQQ_DDR3L} t _{DVBQQ_LPDDR2} t _{DVBQQ_LPDDR3}	Data Output Valid before DQS Input	All Devices	—	-0.26	—	— 0.317	—	— 0.374	ns + 1/2 UI
t _{DVADQ_DDR2} t _{DVADQ_DDR3} t _{DVADQ_DDR3L} t _{DVADQ_LPDDR2} t _{DVADQ_LPDDR3}	Data Output Valid after DQS Input	All Devices	0.26	—	0.317	—	0.374	—	ns + 1/2 UI

Table 3.22. ECP5/ECP5-5G External Switching Characteristics (Continued)

3.19. sysCLOCK PLL Timing

Over recommended operating conditions.

Table 3.23. sysCLOCK PLL Timing

Parameter	Descriptions	Conditions	Min	Max	Units
f_{IN}	Input Clock Frequency (CLKI, CLKFB)	—	8	400	MHz
f_{OUT}	Output Clock Frequency (CLKOP, CLKOS)	—	3.125	400	MHz
f_{VCO}	PLL VCO Frequency	—	400	800	MHz
f_{PFD}^3	Phase Detector Input Frequency	—	10	400	MHz
AC Characteristics					
t_{DT}	Output Clock Duty Cycle	—	45	55	%
t_{PH4}	Output Phase Accuracy	—	–5	5	%
t_{OPJIT}^1	Output Clock Period Jitter	$f_{OUT} \geq 100$ MHz	—	100	ps p-p
		$f_{OUT} < 100$ MHz	—	0.025	UIPP
	Output Clock Cycle-to-Cycle Jitter	$f_{OUT} \geq 100$ MHz	—	200	ps p-p
		$f_{OUT} < 100$ MHz	—	0.050	UIPP
	Output Clock Phase Jitter	$f_{PFD} \geq 100$ MHz	—	200	ps p-p
		$f_{PFD} < 100$ MHz	—	0.011	UIPP
t_{SPO}	Static Phase Offset	Divider ratio = integer	—	400	ps p-p
t_W	Output Clock Pulse Width	At 90% or 10%	0.9	—	ns
t_{LOCK}^2	PLL Lock-in Time	—	—	15	ms
t_{UNLOCK}	PLL Unlock Time	—	—	50	ns
t_{IPJIT}	Input Clock Period Jitter	$f_{PFD} \geq 20$ MHz	—	1,000	ps p-p
		$f_{PFD} < 20$ MHz	—	0.02	UIPP
t_{HI}	Input Clock High Time	90% to 90%	0.5	—	ns
t_{LO}	Input Clock Low Time	10% to 10%	0.5	—	ns
t_{RST}	RST/ Pulse Width	—	1	—	ms
t_{RSTREC}	RST Recovery Time	—	1	—	ns
t_{LOAD_REG}	Min Pulse for CIB_LOAD_REG	—	10	—	ns
$t_{ROTATE-SETUP}$	Min time for CIB dynamic phase controls to be stable fore CIB_ROTATE	—	5	—	ns
$t_{ROTATE-WD}$	Min pulse width for CIB_ROTATE to maintain “0” or	—	4	—	VCO cycles

Notes:

1. Jitter sample is taken over 10,000 samples for Periodic jitter, and 2,000 samples for Cycle-to-Cycle jitter of the primary PLL output with clean reference clock with no additional I/O toggling.
2. Output clock is valid after t_{LOCK} for PLL reset and dynamic delay adjustment.
3. Period jitter and cycle-to-cycle jitter numbers are guaranteed for $f_{PFD} > 10$ MHz. For $f_{PFD} < 10$ MHz, the jitter numbers may not be met in certain conditions.

3.25. PCI Express Electrical and Timing Characteristics

3.25.1. PCIe (2.5 Gb/s) AC and DC Characteristics

Over recommended operating conditions.

Table 3.30. PCIe (2.5 Gb/s)

Symbol	Description	Test Conditions	Min	Typ	Max	Unit
Transmit¹						
UI	Unit interval	—	399.88	400	400.12	ps
V _{TX-DIFF_P-P}	Differential peak-to-peak output	—	0.8	1.0	1.2	V
V _{TX-DE-RATIO}	De-emphasis differential output voltage ratio	—	–3	–3.5	–4	dB
V _{TX-CM-AC_P}	RMS AC peak common-mode output voltage	—	—	—	20	mV
V _{TX-RCV-DETECT}	Amount of voltage change allowed during receiver detection	—	—	—	600	mV
V _{TX-CM-DC}	Tx DC common mode voltage	—	0	—	V _{CCHTX}	V
I _{TX-SHORT}	Output short circuit current	V _{TX-D+} =0.0 V V _{TX-D-} =0.0 V	—	—	90	mA
Z _{TX-DIFF-DC}	Differential output impedance	—	80	100	120	Ω
RL _{TX-DIFF}	Differential return loss	—	10	—	—	dB
RL _{TX-CM}	Common mode return loss	—	6.0	—	—	dB
T _{TX-RISE}	Tx output rise time	20% to 80%	0.125	—	—	UI
T _{TX-FALL}	Tx output fall time	20% to 80%	0.125	—	—	UI
L _{TX-SKEW}	Lane-to-lane static output skew for all lanes in port/link	—	—	—	1.3	ns
T _{TX-EYE}	Transmitter eye width	—	0.75	—	—	UI
T _{TX-EYE-MEDIAN-TO-MAX-JITTER}	Maximum time between jitter median and maximum deviation from median	—	—	—	0.125	UI
Receive^{1,2}						
UI	Unit Interval	—	399.88	400	400.12	ps
V _{RX-DIFF_P-P}	Differential peak-to-peak input voltage	—	0.34 ³	—	1.2	V
V _{RX-IDLE-DET-DIFF_P-P}	Idle detect threshold voltage	—	65	—	340 ³	mV
V _{RX-CM-AC_P}	RMS AC peak common-mode input voltage	—	—	—	150	mV
Z _{RX-DIFF-DC}	DC differential input impedance	—	80	100	120	Ω
Z _{RX-DC}	DC input impedance	—	40	50	60	Ω
Z _{RX-HIGH-IMP-DC}	Power-down DC input impedance	—	200K	—	—	Ω
RL _{RX-DIFF}	Differential return loss	—	10	—	—	dB
RL _{RX-CM}	Common mode return loss	—	6.0	—	—	dB

Notes:

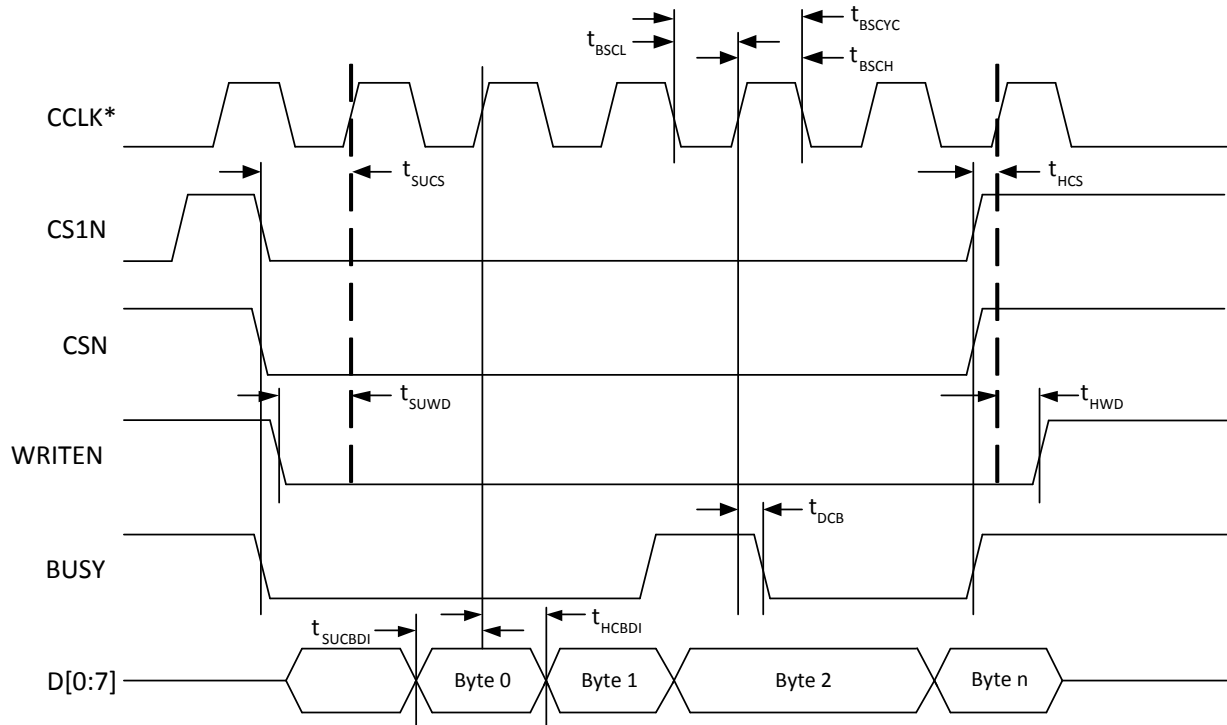
1. Values are measured at 2.5 Gb/s.
2. Measured with external AC-coupling on the receiver.
3. Not in compliance with PCI Express 1.1 standard.

3.26. CPRI LV2 E.48 Electrical and Timing Characteristics – Preliminary

Table 3.32. CPRI LV2 E.48 Electrical and Timing Characteristics

Symbol	Description	Test Conditions	Min	Typ	Max	Unit
Transmit						
UI	Unit Interval	—	203.43	203.45	203.47	ps
T _{DCD}	Duty Cycle Distortion	—	—	—	0.05	UI
J _{UBHPJ}	Uncorrelated Bounded High Probability Jitter	—	—	—	0.15	UI
J _{TOTAL}	Total Jitter	—	—	—	0.3	UI
Z _{RX-DIFF-DC}	DC differential Impedance	—	80	—	120	Ω
T _{SKEW}	Skew between differential signals	—	—	—	9	ps
R _{LTX-DIFF}	Tx Differential Return Loss (S22), including package and silicon	100 MHz < freq < 3.6864 GHz	—	—	–8	dB
		3.6864 GHz < freq < 4.9152 GHz	—	—	–8 + 16.6 *log (freq/3.6864)	dB
R _{LTX-CM}	Tx Common Mode Return Loss, including package and silicon	100 MHz < freq < 3.6864 GHz	6	—	—	dB
I _{TX-SHORT}	Transmitter short-circuit current	—	—	—	100	mA
T _{RISE_FALL-DIFF}	Differential Rise and Fall Time	—	—	—	—	ps
L _{TX-SKEW}	Lane-to-lane output skew	—	—	—	—	ps
Receive						
UI	Unit Interval	—	203.43	203.45	203.47	ps
V _{RX-DIFF-PP}	Differential Rx peak-peak voltage	—	—	—	1.2	V, p-p
V _{RX-EYE_Y1_Y2}	Receiver eye opening mask, Y1 and Y2	—	62.5	—	375	mV, diff
V _{RX-EYE_X1}	Receiver eye opening mask, X1	—	—	—	0.3	UI
T _{RX-TJ}	Receiver total jitter tolerance (not including sinusoidal)	—	—	—	0.6	UI
R _{LRX-DIFF}	Receiver differential Return Loss, package plus silicon	100 MHz < freq < 3.6864 GHz	—	—	–8	dB
		3.6864 GHz < freq < 4.9152 GHz	—	—	–8 + 16.6 *log (freq/3.6864)	dB
R _{LRX-CM}	Receiver common mode Return Loss, package plus silicon	—	6	—	—	dB
Z _{RX-DIFF-DC}	Receiver DC differential impedance	—	80	100	120	Ω

Note: Data is measured with PRBS7 data pattern, not with PRBS-31 pattern.



*In Master Parallel Mode the FPGA provides CCLK (MCLK). In Slave Parallel Mode the external device provides CCLK.

Figure 3.16. sysCONFIG Parallel Port Write Cycle

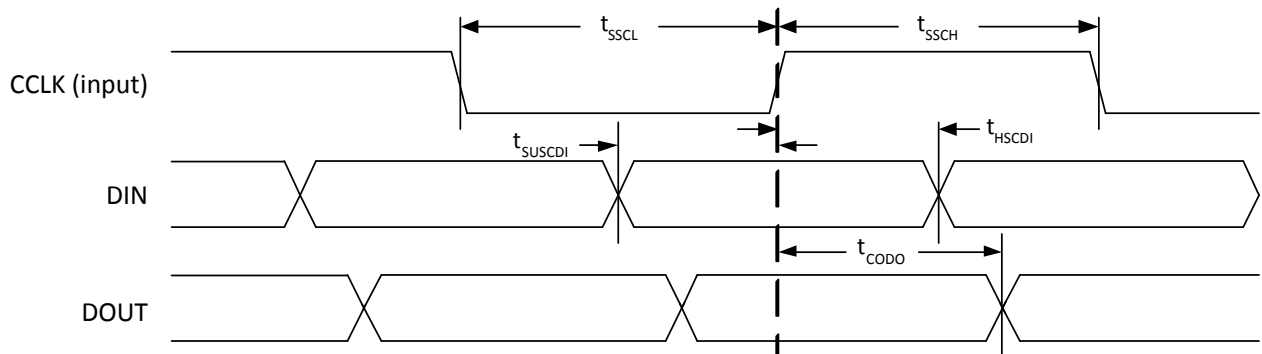


Figure 3.17. sysCONFIG Slave Serial Port Timing

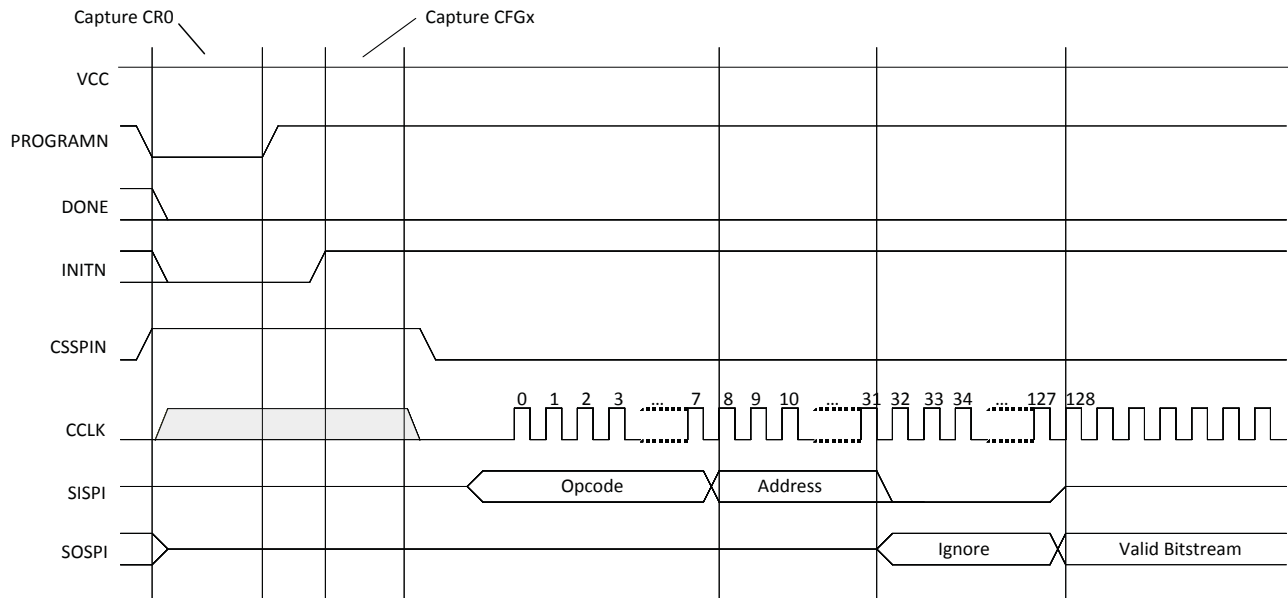


Figure 3.22. Master SPI Configuration Waveforms

3.32. JTAG Port Timing Specifications

Over recommended operating conditions.

Table 3.43. JTAG Port Timing Specifications

Symbol	Parameter	Min	Max	Units
f_{MAX}	TCK clock frequency	—	25	MHz
t_{BTCPH}	TCK [BSCAN] clock pulse width high	20	—	ns
t_{BTCPL}	TCK [BSCAN] clock pulse width low	20	—	ns
t_{BTS}	TCK [BSCAN] setup time	10	—	ns
t_{BTH}	TCK [BSCAN] hold time	8	—	ns
t_{BTRF}	TCK [BSCAN] rise/fall time	50	—	mV/ns
t_{BTCO}	TAP controller falling edge of clock to valid output	—	10	ns
$t_{BTCODIS}$	TAP controller falling edge of clock to valid disable	—	10	ns
t_{BTCOEN}	TAP controller falling edge of clock to valid enable	—	10	ns
t_{BTCRS}	BSCAN test capture register setup time	8	—	ns
t_{BTCRH}	BSCAN test capture register hold time	25	—	ns
t_{BUTCO}	BSCAN test update register, falling edge of clock to valid output	—	25	ns
$t_{BTUODIS}$	BSCAN test update register, falling edge of clock to valid disable	—	25	ns
$t_{BTUPOEN}$	BSCAN test update register, falling edge of clock to valid enable	—	25	ns

Signal Name	I/O	Description
PLL, DLL and Clock Functions (Continued)		
[L/R]DQS[group_num]	I/O	DQS input/output pads: T (top), R (right), group_num = ball number associated with DQS[T] pin.
[T/R]]DQ[group_num]	I/O	DQ input/output pads: T (top), R (right), group_num = ball number associated with DQS[T] pin.
Test and Programming (Dedicated Pins)		
TMS	I	Test Mode Select input, used to control the 1149.1 state machine. Pull-up is enabled during configuration. This is a dedicated input pin.
TCK	I	Test Clock input pin, used to clock the 1149.1 state machine. No pull-up enabled. This is a dedicated input pin.
TDI	I	Test Data in pin. Used to load data into device using 1149.1 state machine. After power-up, this TAP port can be activated for configuration by sending appropriate command. (Note: once a configuration port is selected it is locked. Another configuration port cannot be selected until the power-up sequence). Pull-up is enabled during configuration. This is a dedicated input pin.
TDO	O	Output pin. Test Data Out pin used to shift data out of a device using 1149.1. This is a dedicated output pin.
Configuration Pads (Used during sysCONFIG)		
CFG[2:0]	I	Mode pins used to specify configuration mode values latched on rising edge of INITN. During configuration, a pull-up is enabled. These are dedicated pins.
INITN	I/O	Open Drain pin. Indicates the FPGA is ready to be configured. During configuration, a pull-up is enabled. This is a dedicated pin.
PROGRAMN	I	Initiates configuration sequence when asserted low. This pin always has an active pull-up. This is a dedicated pin.
DONE	I/O	Open Drain pin. Indicates that the configuration sequence is complete, and the startup sequence is in progress. This is a dedicated pin.
CCLK	I/O	Input Configuration Clock for configuring an FPGA in Slave SPI, Serial, and CPU modes. Output Configuration Clock for configuring an FPGA in Master configuration modes (Master SPI, Master Serial). This is a dedicated pin.
HOLDN/DI/BUSY/CSSPIN/CEN	I/O	Parallel configuration mode busy indicator. SPI/SPI mode data output. This is a shared I/O pin. This is a shared I/O pin. When not in configuration, it can be used as general purpose I/O pin.
CSN/SN	I/O	Parallel configuration mode active-low chip select. Slave SPI chip select. This is a shared I/O pin. When not in configuration, it can be used as general purpose I/O pin.
CS1N	I	Parallel configuration mode active-low chip select. This is a shared I/O pin. When not in configuration, it can be used as general purpose I/O pin.
WRITEN	I	Write enable for parallel configuration modes. This is a shared I/O pin. When not in configuration, it can be used as general purpose I/O pin.
DOUT/CSO	O	Serial data output. Chip select output. SPI/SPI mode chip select. This is a shared I/O pin. When not in configuration, it can be used as general purpose I/O pin.
DO/MOSI/IOO	I/O	Parallel configuration I/O. Open drain during configuration. When in SPI modes, it is an output in Master mode, and input in Slave mode. This is a shared I/O pin. When not in configuration, it can be used as general purpose I/O pin.